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Application No. <u>10/786,726</u>	Prepared by <u>DLA</u>	Tracking Number <u>05995918</u>	
Examiner-GAU <u>Hoang - 2818</u>	Date <u>9/17/04</u>	Week Date <u>8/16/04</u>	
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c. Continuing Data	h. Microfiche Appendix	m. Searched Column	r. Abstract
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**INFORMATION DISCLOSURE
 STATEMENT BY APPLICANT**
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Complete if Known

Application Number	10/786726
Filing Date	February 25, 2004
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown
Examiner Name	Unknown

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Attorney Docket No: 303.680US3

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Examiner Name	Unknown

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Sheet 3 of 3		Attorney Docket No: 303.680US3

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